

New Folder Name Simplified Analysis of the
Shot Noise Limited Sensitivity of an Externally
Modulated Interferometer

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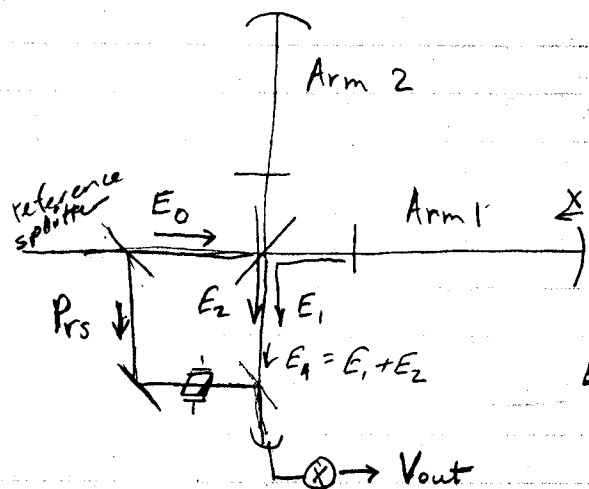
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David, here is my "simplified analysis of the shot noise limited sensitivity of an externally modulated interferometer." It exceeds by a factor of three the one-page limit I had specified. To try to atone for this, I'm willing to talk you through it. I think you will find that most of the space is consumed by diagrams and words of explanation, rather than cryptic equations.

— Martin.

Simplified Analysis of the Shot-Noise Limited Sensitivity of an Externally Modulated Interferometer.



E_0 - field incident on BS
 E_1 - field reflected onto PD from arm 1

Assume length of Arm 2 fixed. Displacement of Arm 1 end mirror is x .

$$|E_1| = \frac{1}{2} |E_0| \quad (1 \text{ transmission, } 1 \text{ refl. " of BS})$$

$$\frac{dE_1}{dx} = 4k \frac{1}{1-r_{in}} i E_1$$

r_{in} - FP input mirror amplitude reflectivity
 $= \sqrt{1-0.03} \approx 0.985$

carrier at antisymmetric portion of reference splitter

$$E_A(x) = E_1(x) + E_2$$

$$\frac{dE_A}{dx} = \frac{4k}{1-r_{in}} i \left(\frac{1}{2} |E_0| \right)$$

factor - 4 because $\frac{d\phi}{dx} = 2kx$ and because phase changes twice as fast outside cavity

$$\text{Let } E_{rs1} = \sqrt{2P_{rs}/E_0} J_1(\Gamma_{opt})$$

P_{rs} - power picked off
 $\Gamma_{opt} \approx 1.84$

then, for $x=0$, field on photodiode is:

$$E_{rs1} e^{i\omega t} - E_{rs1} e^{-i\omega t}$$

Instantaneous Power on photodiode, in presence of carrier field $E_A(x)$:

$$P_{PD}(t) = \frac{1}{2} E_0 | E_{rs1} e^{i\omega t} + E_A(x) - E_{rs1} e^{-i\omega t} |$$

Note $|z_1 + z_2 + z_3|^2 = |z_1|^2 + |z_2|^2 + |z_3|^2 + \sum_{j>i} 2 \operatorname{Re}\{z_i z_j^*\}$

$$P_{PD}(t) = \frac{1}{2} \epsilon_0 \left[2 \operatorname{Re} \left\{ E_A(x) \overset{\sqrt{\epsilon R}}{\text{Ers}_1} \left(e^{-i\omega t} - e^{i\omega t} \right) \right\} \right. \\ \left. + \text{DC} \ \& \ 2\omega \text{ terms} \right]$$

$$= 2 \epsilon_0 \operatorname{Im} \{ E_A(x) \} \text{Ers}_1 \sin \omega t + \text{DC} \ \& \ 2\omega \text{ terms}$$

Suppose photo diode / demod do the following:

$$V_{out} = \frac{1}{T} \int_{t-T}^t P(t) \sin \omega t \, dt$$

then $V_{out}(x) = \epsilon_0 \operatorname{Im} \{ E_A(x) \} \text{Ers}_1$

$$\frac{dV_{out}(x)}{dx} = \frac{2k}{1-r_{in}} \epsilon_0 |E_0| \text{Ers}_1$$

$$= \frac{4k}{1-r_{in}} \overset{\text{incident laser power}}{P_{laser}} \left(\sqrt{1-R_{rs}} \right) \left(\sqrt{R_{rs}} J_1(\Gamma_{opt}) \right)$$

↑
reference splitter (power) reflectivity

Shot noise:

$$S_{P_{PD}}^{1/2}(f) = \sqrt{2 h \nu P_{rs}}$$

$$S_{V_{out}}^{1/2}(f) = \sqrt{h \nu P_{rs}}$$

since half of shot noise power goes into quadrature demod phase

Finally

$$S_x^{1/2}(f) = \frac{S_{V_{out}}^{1/2}(f)}{\frac{dV_{out}}{dx}} = \frac{\sqrt{h \nu P_{laser} R_{rs}}}{\frac{4k}{1-r_{in}} P_{laser} \sqrt{1-R_{rs}} \sqrt{R_{rs}} J_1(\Gamma_{opt})}$$

$$S_x^{1/2}(f) = \sqrt{\frac{h\nu}{P_{\text{rec}}}} \frac{1-r_{\text{in}}}{4k} \frac{1}{J_1(\Gamma_{\text{opt}})}$$

$$S_h^{1/2}(f) = S_x^{1/2}(f) / 4000 \text{ m}$$

Numerically, for

$$P_{\text{rec}} = 1.54 \text{ W} \cdot 37.9 \quad \swarrow \text{rec. gain}$$

$$J_1(\Gamma_{\text{opt}}) = 0.582$$

$$h\nu = 3.87 \times 10^{-19} \text{ J}$$

$$k = 1.22 \times 10^7 \text{ m}^{-1}$$

$$r_{\text{in}} = 0.985$$

$$S_x^{1/2} = 4.33 \times 10^{-20}$$

$$S_h^{1/2} = 1.08 \times 10^{-23}$$